

BAS16J Single high-speed switching diode Rev. 01 — 8 March 2007

Product data sheet

1. Product profile

1.1 General description

Single high-speed switching diode, encapsulated in a SOD323F (SC-90) very small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- High switching speed: $t_{rr} \le 4$ ns
- Low leakage current
- Repetitive peak reverse voltage: V_{RRM} ≤ 100 V
- Excellent coplanarity and improved thermal behavior

1.3 Applications

- High-speed switching
- General-purpose switching

- Low capacitance: C_d ≤ 1.5 pF
- Reverse voltage: $V_R \le 100 V$
- Very small and flat lead SMD plastic package
- Voltage clampingReverse polarity protection

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		<u>[1]</u> _	-	250	mA
I _R	reverse current	V _R = 75 V	-	-	1	μA
V _R	reverse voltage		-	-	100	V
t _{rr}	reverse recovery time		[2] _	-	4	ns

[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.



2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Symbol
1	cathode	[1]	1.4
2	anode		K
			sym006

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BAS16J	SC-90	plastic surface-mounted package; 2 leads	SOD323F		

4. Marking

Table 4.	Marking codes	
Type num	ber	Marking code
BAS16J		AR

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	100	V
V _R	reverse voltage		-	100	V
I _F	forward current		<u>[1]</u> _	250	mA
I _{FRM}	repetitive peak forward current	$\begin{array}{l} t_p \leq 0.5 \text{ ms;} \\ \delta \leq 0.25 \end{array}$	-	500	mA
I _{FSM}	non-repetitive peak forward current	square wave	[2]		
		t _p = 100 μs	-	3.3	А
		t _p = 1 ms	-	2	А
		t _p = 10 ms	-	1.5	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[3][4]</u> _	550	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

[2] $T_i = 25 \,^{\circ}C$ prior to surge.

[3] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[4] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1][2]</u> _	-	230	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[3]</u> _	-	55	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[2] Reflow soldering is the only recommended soldering method.

[3] Soldering point of cathode tab.

7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _F forward voltage	forward voltage		<u>[1]</u>				
		I _F = 1 mA		-	-	715	mV
	I _F = 10 mA		-	-	855	mV	
	I _F = 50 mA		-	-	1	V	
		I _F = 150 mA		-	-	1.25	V
I _R	I _R reverse current	V _R = 25 V		-	-	30	nA
		V _R = 75 V		-	-	1	μΑ
		V_R = 25 V; T_j = 150 °C		-	-	30	μΑ
		V_R = 75 V; T_j = 150 °C		-	-	50	μΑ
C _d	diode capacitance	$V_R = 0 V$; f = 1 MHz		-	-	1.5	pF
t _{rr}	reverse recovery time		[2]	-	-	4	ns
V _{FR}	forward recovery voltage		[3]	-	-	1.75	V

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

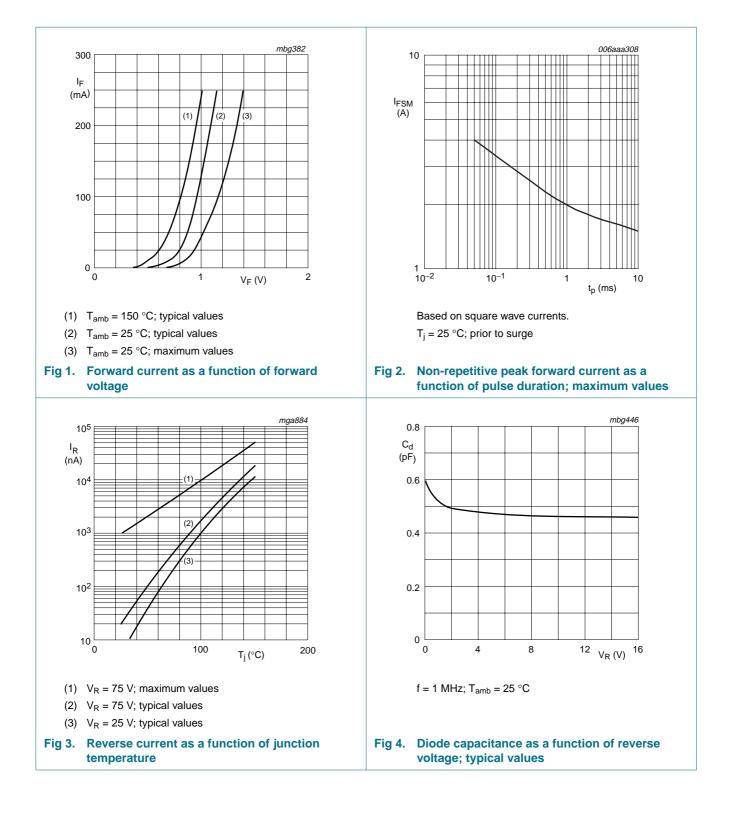
[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

[3] When switched from $I_F = 10$ mA; $t_r = 20$ ns.

BAS16J_1 Product data sheet

BAS16J

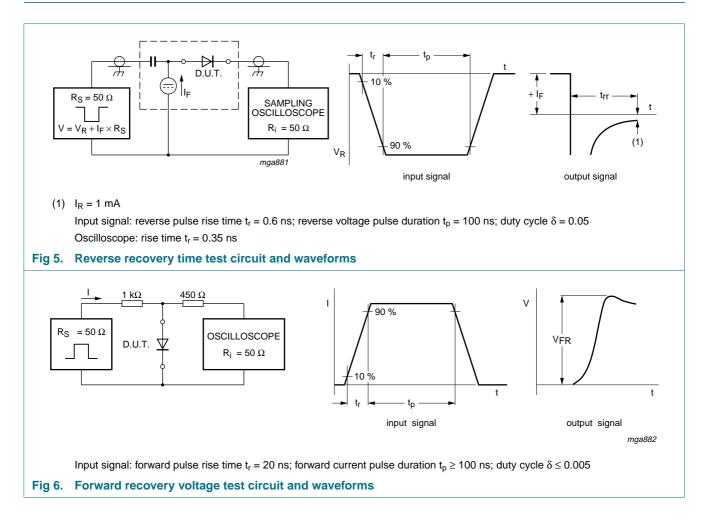
Single high-speed switching diode



BAS16J 1

Single high-speed switching diode

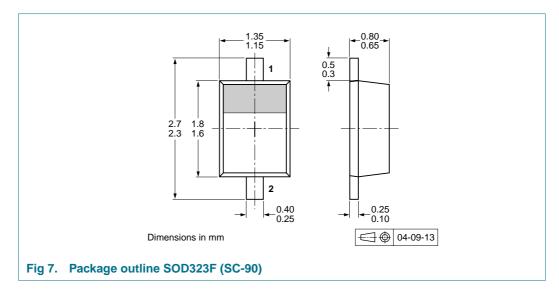
8. Test information



BAS16J_1

Single high-speed switching diode

9. Package outline



10. Packing information

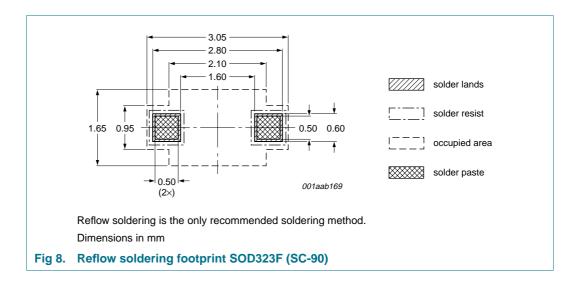
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			3000	10000
BAS16J	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



12. Revision history

Table 9. Revision	n history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BAS16J_1	20070308	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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BAS16J

Single high-speed switching diode

15. Contents

1	Product profile 1
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 3
7	Characteristics 4
8	Test information 6
9	Package outline 7
10	Packing information 7
11	Soldering 7
12	Revision history 8
13	Legal information
13.1	Data sheet status 9
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks
14	Contact information 9
15	Contents 10

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Date of release: 8 March 2007 Document identifier: BAS16J_1

